

## *Technical Supplement*

### **MC68C812A4 3.3V Electrical Characteristics**

The MC68C812A4 is the low-voltage version of the standard MC68HC812A4 microcontroller unit (MCU), a 16-bit device composed of standard on-chip peripheral modules connected by an intermodule bus. Modules include a 16-bit central processing unit (CPU12), a Lite integration module (LIM), two asynchronous serial communications interfaces (SCI0 and SCI1), a serial peripheral interface (SPI), a timer and pulse accumulation module, an 8-bit analog-to-digital converter (ATD), 1-Kbyte RAM, 4-Kbyte EEPROM, and memory expansion logic with chip selects, key wakeup ports, and a phase-locked loop (PLL).

This supplement contains the most accurate electrical information for the MC68C812A4 microcontroller available at the time of publication. The information should be considered preliminary and is subject to change. The following characteristics are contained in this document:

**Table 1 Maximum Ratings**

**Table 2 Thermal Characteristics**

**Table 3 DC Electrical Characteristics**

**Table 4 Supply Current**

**Table 5 ATD Maximum Ratings**

**Table 6 ATD DC Electrical Characteristics**

**Table 7 Analog Converter Characteristics (Operating)**

**Table 8 ATD AC Characteristics (Operating)**

**Table 9 EEPROM Characteristics**

**Table 10 Control Timing**

**Table 11 Peripheral Port Timing**

**Table 12 Non-Multiplexed Expansion Bus Timing**

**Table 13 SPI Timing**

**PRELIMINARY**

**Table 1 Maximum Ratings<sup>1</sup>**

Rating	Symbol	Value	Unit
Supply voltage	$V_{DD}, V_{DDA}, V_{DDX}$	-0.3 to +6.5	V
Input voltage	$V_{IN}$	-0.3 to +6.5	V
Operating temperature range <sup>2</sup> MC68C812A4PV5	$T_A$	$T_L$ to $T_H$ 0 to +70	°C
Storage temperature range	$T_{stg}$	-55 to +150	°C
Current drain per pin <sup>3</sup> Excluding $V_{DD}$ and $V_{SS}$	$I_{IN}$	±25	mA
$V_{DD}$ differential voltage	$V_{DD}-V_{DDX}$	6.5	V

NOTES:

1. Permanent damage can occur if maximum ratings are exceeded. Exposures to voltages or currents in excess of recommended values affects device reliability. Device modules may not operate normally while being exposed to electrical extremes.
2. Refer to MC68HC812A4TS/D Technical Summary for complete part numbers.
3. One pin at a time, observing maximum power dissipation limits. Internal circuitry protects the inputs against damage caused by high static voltages or electric fields; however, normal precautions are necessary to avoid application of any voltage higher than maximum-rated voltages to this high-impedance circuit. Extended operation at the maximum ratings can adversely affect device reliability. Tying unused inputs to an appropriate logic voltage level (either GND or  $V_{DD}$ ) enhances reliability of operation.

**Table 2 Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Average junction temperature	$T_J$	$T_A + (P_D \times \Theta_{JA})$	°C
Ambient temperature	$T_A$	User-determined	°C
Package thermal resistance (junction-to-ambient) 112-pin thin quad flat pack (TQFP)	$\Theta_{JA}$	39	°C/W
Total power dissipation <sup>1</sup>	$P_D$	$\frac{P_{INT} + P_{I/O}}{K}$ $\bar{T}_J + 273^\circ\text{C}$	W
Device internal power dissipation	$P_{INT}$	$I_{DD} \times V_{DD}$	W
I/O pin power dissipation <sup>2</sup>	$P_{I/O}$	User-determined	W
A constant <sup>3</sup>	K	$P_D \times (T_A + 273^\circ\text{C}) + \Theta_{JA} \times P_D^2$	W · °C

NOTES:

1. This is an approximate value, neglecting  $P_{I/O}$ .
2. For most applications  $P_{I/O} \ll P_{INT}$  and can be neglected.
3. K is a constant pertaining to the device. Solve for K with a known  $T_A$  and a measured  $P_D$  (at equilibrium). Use this value of K to solve for  $P_D$  and  $T_J$  iteratively for any value of  $T_A$ .

**Table 3 DC Electrical Characteristics**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , unless otherwise noted

Characteristic	Symbol	Min	Max	Unit
Input high voltage, all inputs	$V_{IH}$	$0.7 \times V_{DD}$	$V_{DD} + 0.3$	V
Input low voltage, all inputs	$V_{IL}$	$V_{SS} - 0.3$	$0.2 \times V_{DD}$	V
Output high voltage All I/O and output pins Normal drive strength $I_{OH} = -10.0 \mu\text{A}$ $I_{OH} = -0.8 \text{ mA}$  Reduced drive strength $I_{OH} = -4.0 \mu\text{A}$ $I_{OH} = -0.3 \text{ mA}$	$V_{OH}$	$V_{DD} - 0.2$ $V_{DD} - 0.8$  $V_{DD} - 0.2$ $V_{DD} - 0.8$	— —  — —	V V  V V
Output low voltage, All I/O and output pins, normal drive strength $I_{OL} = 10.0 \mu\text{A}$ $I_{OL} = 1.6 \text{ mA}$  EXTAL, PAD[7:0], $V_{RH}$ , $V_{RL}$ , $V_{FP}$ , $\overline{XIRQ}$ , reduced drive strength $I_{OL} = 3.6 \mu\text{A}$ $I_{OL} = 0.6 \text{ mA}$	$V_{OL}$	— —  — —	$V_{SS} + 0.2$ $V_{SS} + 0.4$  $V_{SS} + 0.2$ $V_{SS} + 0.4$	V V  V V
Input leakage current <sup>1</sup> all inputs except $\overline{IRQ}$ , PAD7, and XFC $V_{in} = V_{DD}$ or $V_{SS}$ $\overline{IRQ}$ , PAD7, XFC	$I_{in}$	— —	$\pm 1$ $\pm 10$	$\mu\text{A}$ $\mu\text{A}$
Three-state leakage, I/O ports, BKGD, and $\overline{RESET}$	$I_{OZ}$	—	$\pm 2.5$	$\mu\text{A}$
Input capacitance All input pins and ATD pins (non-sampling) ATD pins (sampling) All I/O pins	$C_{in}$	— — —	10 15 20	pF pF pF
Output load capacitance All outputs except PS[7:4] PS[7:4]	$C_L$	— —	90 130	pF pF
Active pull-up, pull-down current $\overline{IRQ}$ , $\overline{XIRQ}$ , ECLK, $\overline{LSTRB}$ , $R/\overline{W}$ , BKGD, MODA, MODB, ARST Ports A, B, C, D, F, G, H, J, S, T	$I_{APU}$	50	500	$\mu\text{A}$
RAM standby voltage, power down	$V_{SB}$	2.0	—	V
RAM standby current	$I_{SB}$	—	1	mA

NOTES:

1. Specification is for parts in the 0 to +70°C range. Higher temperature ranges will result in increased current leakage.

**PRELIMINARY**

**Table 4 Supply Current**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , unless otherwise noted

Characteristic	Symbol	4 MHz	5 MHz	Unit	
Maximum total supply current	<b>RUN:</b>	Single-chip mode	15	17	mA
		Expanded mode	21	25	mA
	<b>WAIT:</b> (All peripheral functions shut down)	Single-chip mode	3	3.5	mA
		Expanded mode	3	3.5	mA
	<b>STOP:</b>				
	Single-chip mode, no clocks	$S_{IDD}$	250	250	$\mu\text{A}$
Maximum power dissipation <sup>1</sup>	Single-chip mode	54	62	mW	
	Expanded mode	76	90	mW	

NOTES:

1. Includes  $I_{DD}$  and  $I_{DDA}$ .

Note:  $I_{DD}$  is tested with a rail-to-rail square wave on EXTAL

**Table 5 ATD Maximum Ratings**

Characteristic	Symbol	Value	Units
ATD reference voltage	$V_{RH} \leq V_{DDA}$	-0.3 to +6.5	V
	$V_{RL} \geq V_{SSA}$	-0.3 to +6.5	V
$V_{SS}$ differential voltage	$ V_{SS} - V_{SSA} $	0.1	V
$V_{DD}$ differential voltage	$ V_{DD} - V_{DDA} $	6.5	V
	$V_{DD} - V_{DDX}$	6.5	V
$V_{REF}$ differential voltage	$ V_{RH} - V_{RL} $	6.5	V
Reference to supply differential voltage	$ V_{RH} - V_{DDA} $	6.5	V
	$ V_{RL} - V_{SSA} $	6.5	V

PRELIMINARY

**Table 6 ATD DC Electrical Characteristics**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , ATD Clock = 2 MHz, unless otherwise noted

Characteristic	Symbol	Min	Max	Unit
Analog supply voltage	$V_{DDA}$	3.0	3.6	V
Analog supply current      Normal operation	$I_{DDA}$		1.0	mA
Reference voltage, low	$V_{RL}$	$V_{SSA}$	$V_{DDA}/2$	V
Reference voltage, high	$V_{RH}$	$V_{DDA}/2$	$V_{DDA}$	V
$V_{REF}$ differential reference voltage <sup>1</sup>	$V_{RH}-V_{RL}$	3.0	3.6	V
Input voltage <sup>2</sup>	$V_{INDC}$	$V_{SSA}$	$V_{DDA}$	V
Input current, off channel <sup>3</sup>	$I_{OFF}$		100	nA
Reference supply current	$I_{REF}$		250	$\mu\text{A}$
Input capacitance      Not Sampling Sampling	$C_{INN}$ $C_{INS}$		10 15	pF pF

**NOTES:**

1. Accuracy is guaranteed at  $V_{RH} - V_{RL} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ .
2. To obtain full-scale, full-range results,  $V_{SSA} \leq V_{RL} \leq V_{INDC} \leq V_{RH} \leq V_{DDA}$ .
3. Maximum leakage occurs at maximum operating temperature. Current decreases by approximately one-half for each 10°C decrease from maximum temperature.

**PRELIMINARY**

**Table 7 Analog Converter Characteristics (Operating)**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , ATD Clock = 2 MHz, unless otherwise noted

Characteristic	Symbol	Min	Typical	Max	Unit
8-bit resolution <sup>1</sup>	2 counts		24		mV
Differential non-linearity <sup>2</sup>	DNL	-0.5		+0.5	count
Integral non-linearity <sup>2</sup>	INL	-1		+1	count
Absolute error <sup>2,3</sup> 2, 4, 8, and 16 ATD sample clocks	AE	-2		+2	count
Maximum source impedance	$R_S$		20	See note <sup>4</sup>	K $\Omega$

NOTES:

- $V_{RH} - V_{RL} \geq 3.072\text{V}$
- At  $V_{REF} = 3.072\text{V}$ , one 8-bit count = 12 mV.
- Eight-bit absolute error of 2 counts (24 mV) includes 1/2 count (6 mV) inherent quantization error and 1 1/2 counts (18 mV) circuit (differential, integral, and offset) error.
- Maximum source impedance is application-dependent. Error resulting from pin leakage depends on junction leakage into the pin and on leakage due to charge-sharing with internal capacitance. Error from junction leakage is a function of external source impedance and input leakage current. Expected error in result value due to junction leakage is expressed in voltage ( $V_{ERRJ}$ ):

$$V_{ERRJ} = R_S \times I_{OFF}$$

where  $I_{OFF}$  is a function of operating temperature. Charge-sharing effects with internal capacitors are a function of ATD clock speed, the number of channels being scanned, and source impedance. For 8-bit conversions, charge pump leakage is computed as follows:

$$V_{ERRJ} = .25\text{pF} \times V_{DDA} \times R_S \times \text{ATDCLK}/(8 \times \text{number of channels})$$

**Table 8 ATD AC Characteristics (Operating)**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , ATD Clock = 2 MHz, unless otherwise noted

Characteristic	Symbol	Min	Max	Unit
ATD operating clock frequency	$f_{\text{ATDCLK}}$	0.5	2.0	MHz
Conversion time per channel 0.5 MHz $\leq$ $f_{\text{ATDCLK}} \leq$ 2 MHz	$t_{\text{CONV}}$			
18 ATD clocks		9.0	32.0	$\mu\text{s}$
32 ATD clocks		16.0	60.0	$\mu\text{s}$
Stop recovery time $V_{DDA} = 3.3\text{V}$	$t_{\text{SR}}$		50	$\mu\text{s}$

**Table 9 EEPROM Characteristics**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , unless otherwise noted

Characteristic	Symbol	Min	Typical	Max	Unit
Minimum programming clock frequency <sup>1</sup>	$f_{\text{PROG}}$	3.0			MHz
Programming time	$t_{\text{PROG}}$			20	ms
Clock recovery time following STOP, to continue programming	$t_{\text{CRSTOP}}$			$t_{\text{PROG}} + 1$	ms
Erase time	$t_{\text{ERASE}}$			20	ms
Write/erase endurance		10,000	30,000		cycles
Data retention		10			years

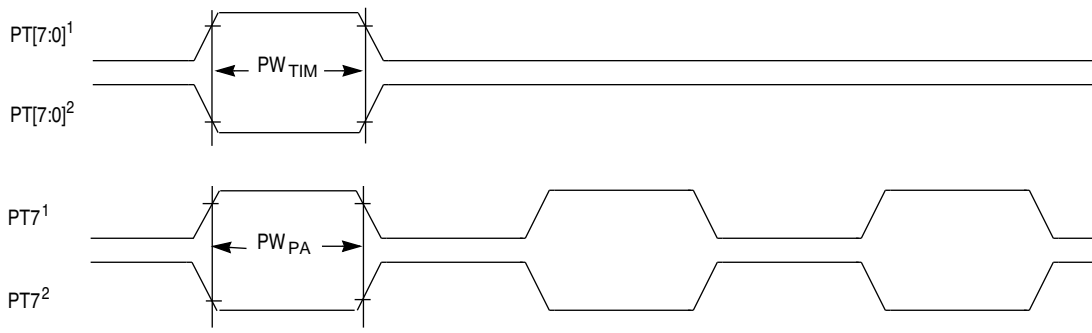
NOTES:

1. RC oscillator must be enabled if programming is desired and  $f_{\text{SYS}} < f_{\text{PROG}}$ .

**Table 10 Control Timing**

Characteristic	Symbol	5.0 MHz		Unit
		Min	Max	
Frequency of operation	$f_o$	dc	5.0	MHz
E-clock period	$t_{\text{cyc}}$	200	—	ns
Crystal frequency	$f_{\text{XTAL}}$	—	10.0	MHz
External oscillator frequency	$2f_o$	dc	10.0	MHz
Processor control setup time $t_{\text{PCSU}} = t_{\text{cyc}}/2 + 30$	$t_{\text{PCSU}}$	130	—	ns
Reset input pulse width To guarantee external reset vector Minimum input time (can be preempted by internal reset)	$PW_{\text{RSTL}}$	32 2	— —	$t_{\text{cyc}}$ $t_{\text{cyc}}$
Mode programming setup time	$t_{\text{MPS}}$	4	—	$t_{\text{cyc}}$
Mode programming hold time	$t_{\text{MPH}}$	10	—	ns
Interrupt pulse width, $\overline{\text{IRQ}}$ , edge-sensitive mode, KWU $PW_{\text{IRQ}} = 2t_{\text{cyc}} + 20$	$PW_{\text{IRQ}}$	420	—	ns
Wait recovery startup time	$t_{\text{WRS}}$	—	4	$t_{\text{cyc}}$
Timer pulse width, input capture pulse accumulator input $PW_{\text{TIM}} = 2t_{\text{cyc}} + 20$	$PW_{\text{TIM}}$	420	—	ns

**PRELIMINARY**

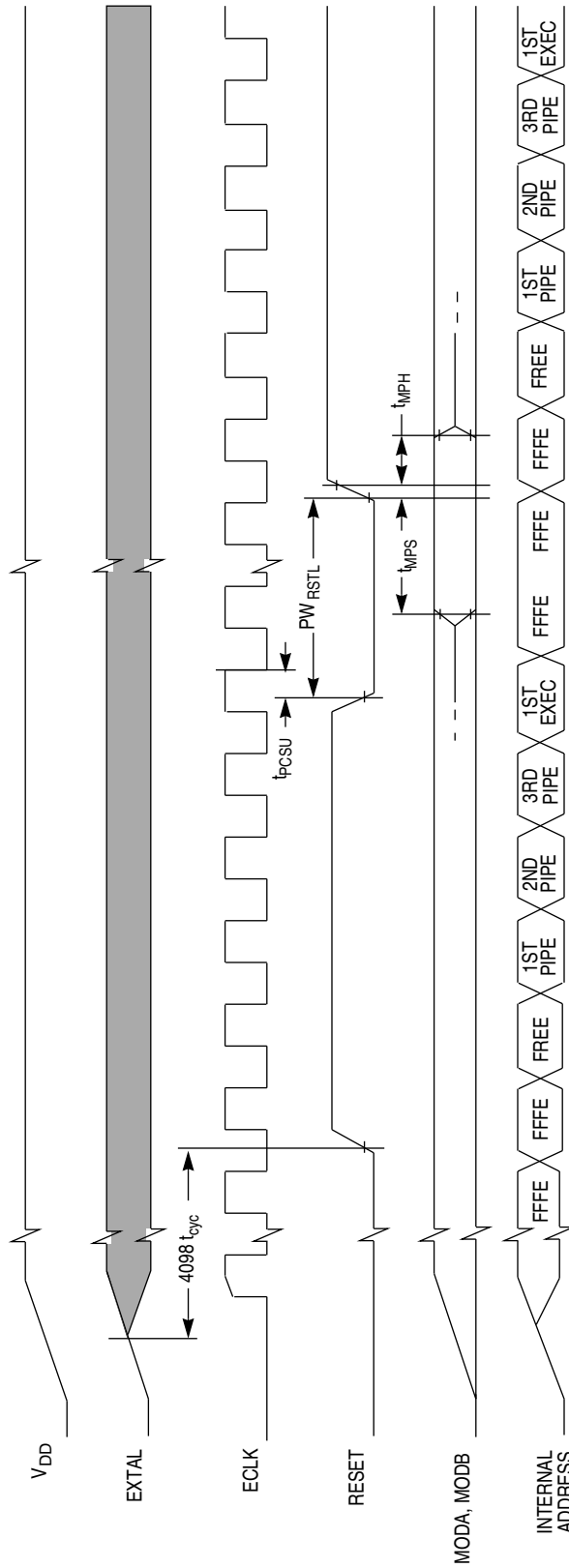


NOTES :  
1. Rising edge sensitive input  
2. Falling edge sensitive input

TIMER INPUT TIMING

Figure 1 Timer Inputs





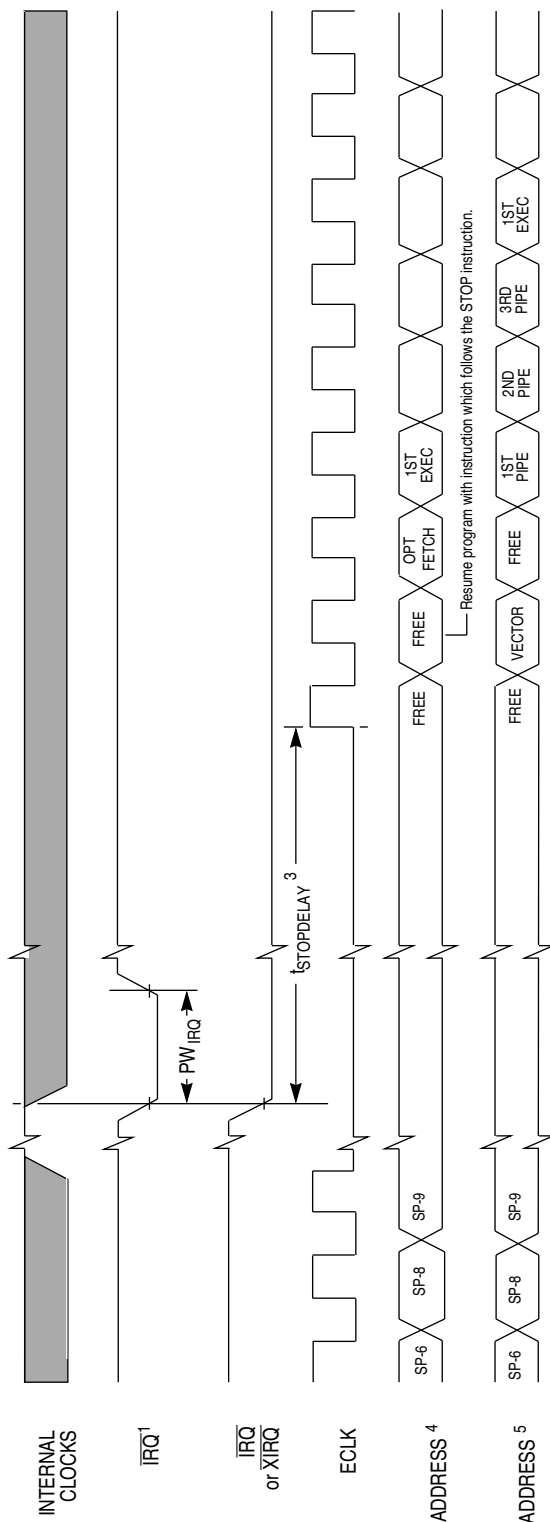
POR EXT RESET TIM

NOTE: Reset timing is subject to change.

Figure 2 POR and External Reset Timing Diagram

**PRELIMINARY**

# PRELIMINARY

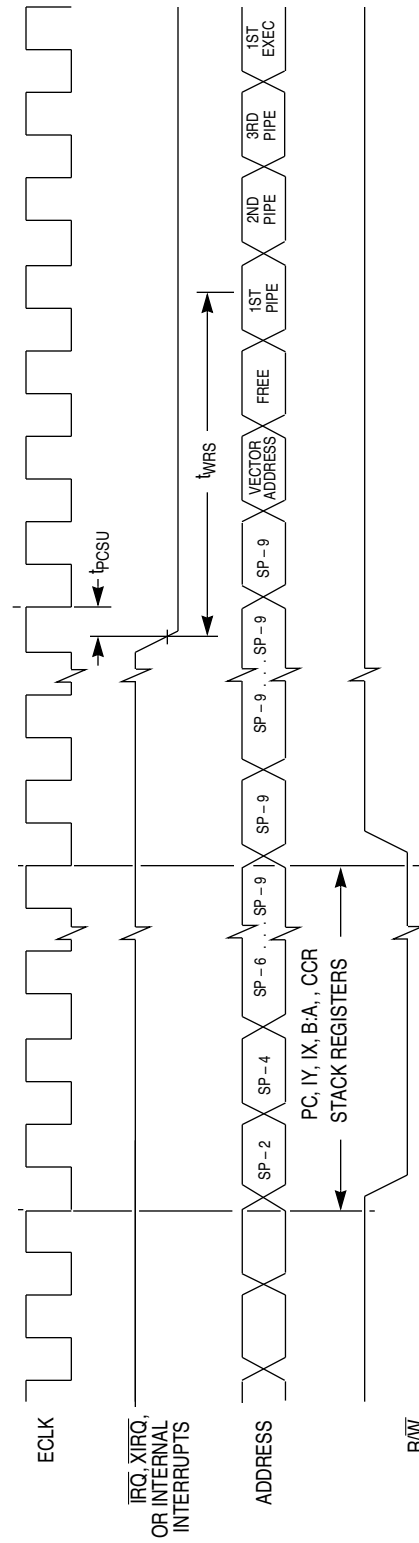


**NOTES:**

1. Edge Sensitive  $\overline{IRQ}$  pin (IRQE bit = 1)
2. Level sensitive  $\overline{IRQ}$  pin (IRQE bit = 0)
3.  $t_{STOPDELAY} = 4098 t_{cyc}$  if DLY bit = 1 or  $2 t_{cyc}$  if DLY = 0.
4.  $\overline{XIRQ}$  with X bit in CCR = 1.
5.  $\overline{IRQ}$  or  $\overline{XIRQ}$  with X bit in CCR = 0).

STOP RECOVERY TIM

**Figure 3 STOP Recovery Timing Diagram**



NOTE: RESET also causes recovery from WAIT.

WAIT RECOVERY TIM

Figure 4 WAIT Recovery Timing Diagram

**PRELIMINARY**

# PRELIMINARY

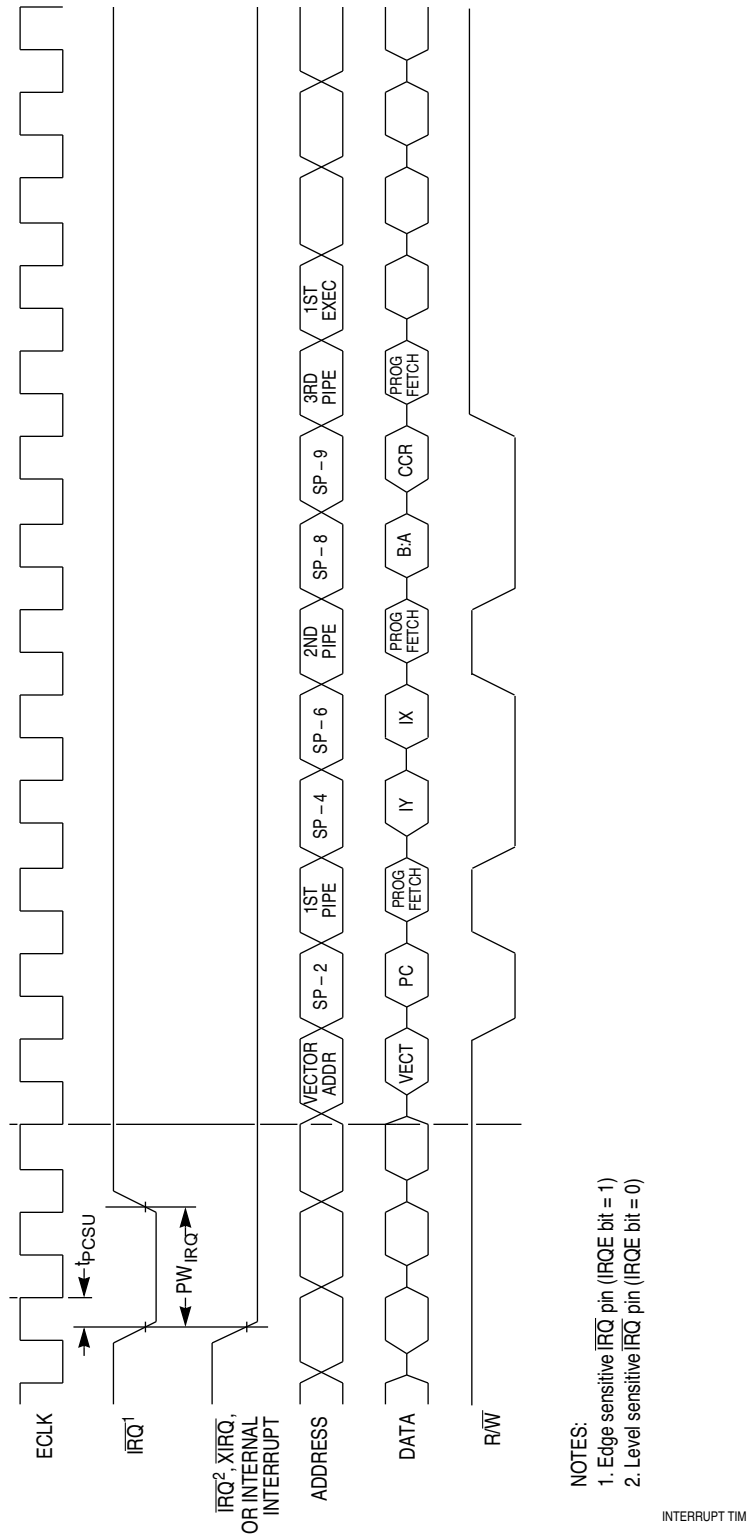
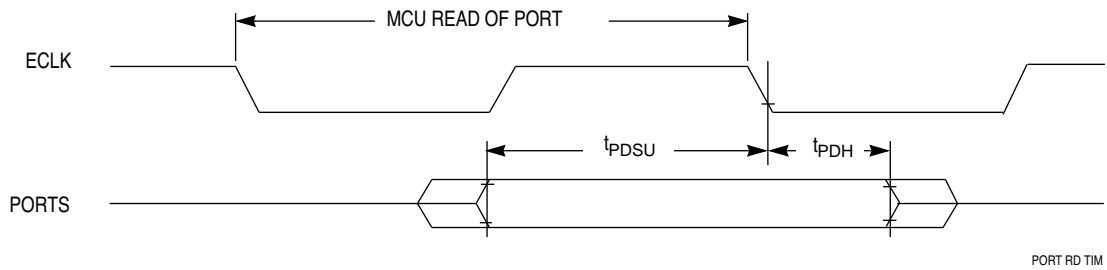


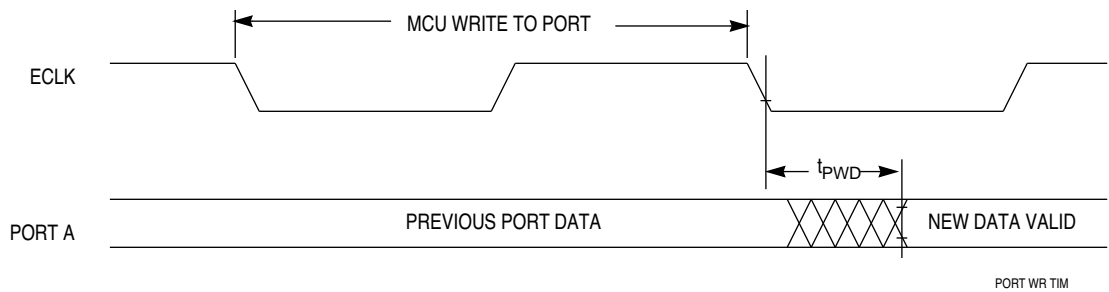
Figure 5 Interrupt Timing Diagram

**Table 11 Peripheral Port Timing**

Characteristic	Symbol	5.0 MHz		Unit
		Min	Max	
Frequency of operation (E-clock frequency)	$f_o$	dc	5.0	MHz
E-clock period	$t_{cyc}$	200	—	ns
Peripheral data setup time MCU read of ports $t_{PDSU} = t_{cyc}/2 + 30$	$t_{PDSU}$	130	—	ns
Peripheral data hold time MCU read of ports	$t_{PDH}$	0	—	ns
Delay time, peripheral data write MCU write to ports	$t_{PWD}$	—	40	ns



**Figure 6 Port Read Timing Diagram**



**Figure 7 Port Write Timing Diagram**

**PRELIMINARY**

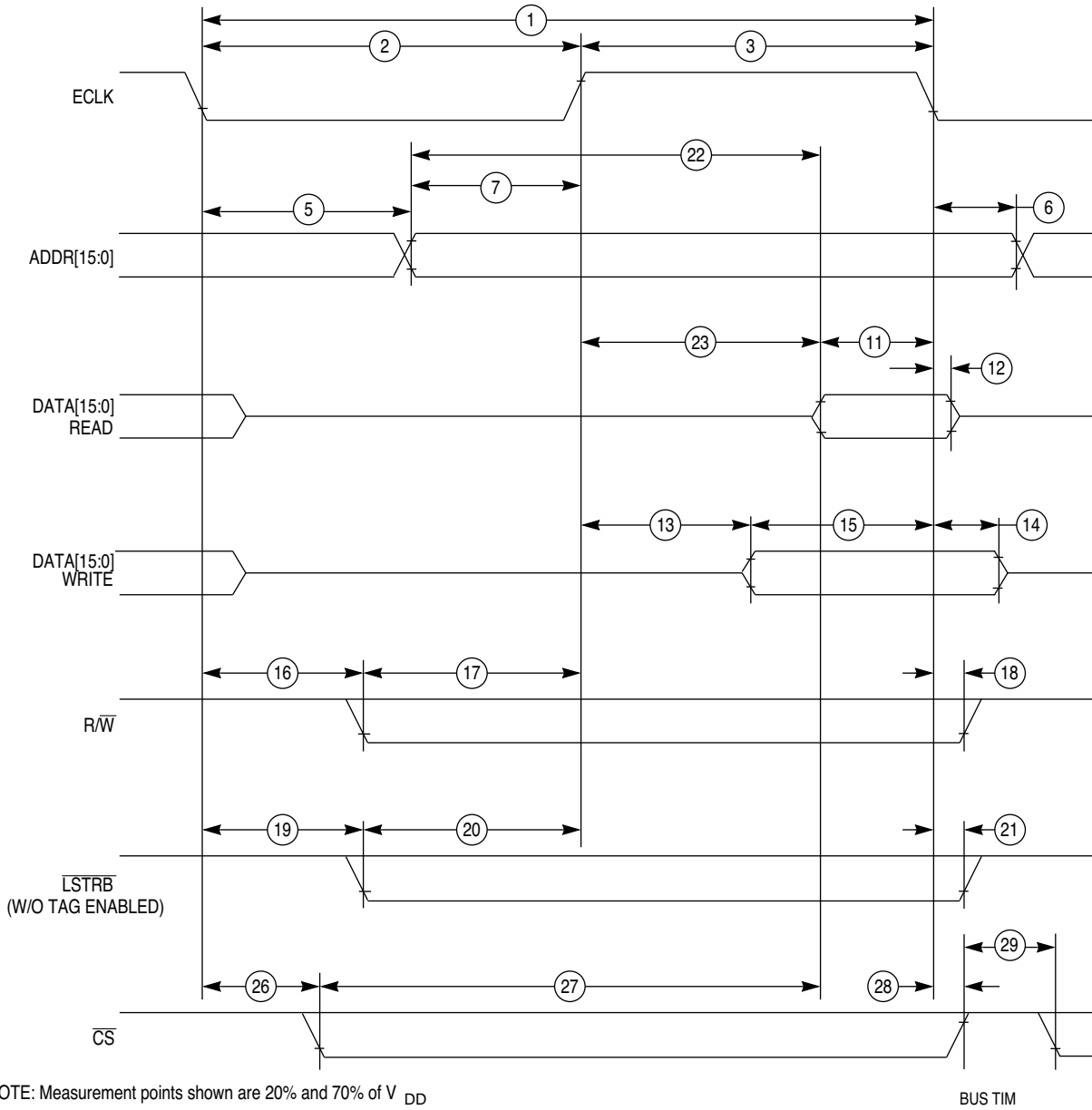
**Table 12 Non-Multiplexed Expansion Bus Timing**

$V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L$  to  $T_H$ , unless otherwise noted

Num	Characteristic <sup>1</sup>	Delay	Symbol	5 MHz		Unit
				Min	Max	
	Frequency of operation (E-clock frequency)		$f_o$	dc	5.0	MHz
1	Cycle time $t_{cyc} = 1/f_o$		$t_{cyc}$	200	—	ns
2	Pulse width, E low $PW_{EL} = t_{cyc}/2 + \text{delay}$	-2	$PW_{EL}$	98	—	ns
3	Pulse width, E high <sup>2</sup> $PW_{EH} = t_{cyc}/2 + \text{delay}$	-2	$PW_{EH}$	98	—	ns
5	Address delay time $t_{AD} = t_{cyc}/4 + \text{delay}$	29	$t_{AD}$	—	79	ns
6	Address hold time	—	$t_{AH}$	20	—	ns
7	Address valid time to E rise $t_{AV} = PW_{EL} - t_{AD}$	—	$t_{AV}$	28	—	ns
11	Read data setup time	—	$t_{DSR}$	30	—	ns
12	Read data hold time	—	$t_{DHR}$	0	—	ns
13	Write data delay time $t_{DDW} = t_{cyc}/4 + \text{delay}$	25	$t_{DDW}$	—	75	ns
14	Write data hold time	—	$t_{DHW}$	20	—	ns
15	Write data setup time <sup>2</sup> $t_{DSW} = PW_{EH} - t_{DDW}$	—	$t_{DSW}$	23	—	ns
16	Read/write delay time $t_{RWD} = t_{cyc}/4 + \text{delay}$	20	$t_{RWD}$	—	70	ns
17	Read/write valid time to E rise $t_{RWV} = PW_{EL} - t_{RWD}$	—	$t_{RWV}$	28	—	ns
18	Read/write hold time	—	$t_{RWH}$	20	—	ns
19	Low strobe delay time $t_{LSD} = t_{cyc}/4 + \text{delay}$	20	$t_{LSD}$	—	70	ns
20	Low strobe valid time to E rise $t_{LSV} = PW_{EL} - t_{LSD}$	—	$t_{LSV}$	28	—	ns
21	Low strobe hold time	—	$t_{LSH}$	20	—	ns
22	Address access time <sup>2</sup> $t_{ACCA} = t_{cyc} - t_{AD} - t_{DSR}$	—	$t_{ACCA}$	—	100	ns
23	Access time from E rise <sup>2</sup> $t_{ACCE} = PW_{EH} - t_{DSR}$	—	$t_{ACCE}$	—	68	ns
26	Chip select delay time $t_{CSD} = t_{cyc}/4 + \text{delay}$	29	$t_{CSD}$	—	79	ns
27	Chip select access time <sup>2</sup> $t_{ACCS} = t_{cyc} - t_{CSD} - t_{DSR}$	—	$t_{ACCS}$	—	100	ns
28	Chip select hold time	—	$t_{CSH}$	0	10	ns
29	Chip select negated time $t_{CSN} = t_{cyc}/4 + \text{delay}$	5	$t_{CSN}$	55	—	ns

NOTES:

1. All timings are calculated for normal port drives.
2. This characteristic is affected by clock stretch.  
Add  $N \times t_{cyc}$  where  $N = 0, 1, 2, \text{ or } 3$ , depending on the number of clock stretches.



**Figure 8 Non-Multiplexed Expansion Bus Timing Diagram**

**PRELIMINARY**

**Table 13 SPI Timing** $V_{DD} = 3.3 \text{ Vdc} \pm 0.3\text{V}$ ,  $V_{SS} = 0 \text{ Vdc}$ ,  $T_A = T_L \text{ to } T_H$ , 130 pF load on all SPI pins<sup>1</sup>

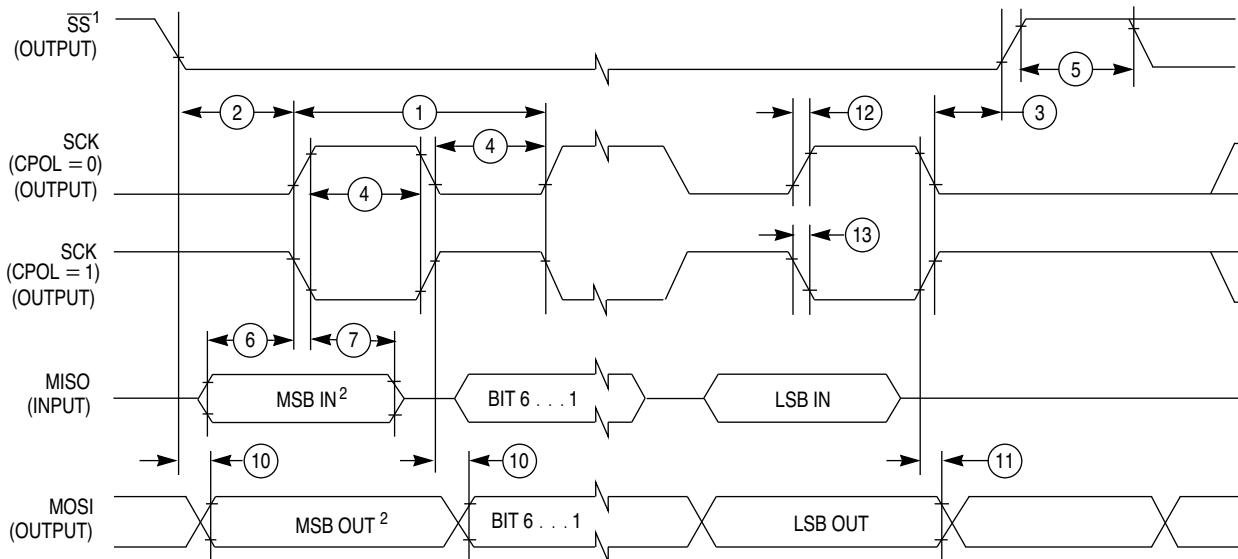
Num	Function	Symbol	Min	Max	Unit
	Operating Frequency Master Slave	$f_{op}$	DC DC	1/2 1/2	E-clock frequency
1	SCK Period Master Slave	$t_{sck}$	2 2	256 —	$t_{cyc}$ $t_{cyc}$
2	Enable Lead Time Master Slave	$t_{lead}$	1/2 1	— —	$t_{sck}$ $t_{cyc}$
3	Enable Lag Time Master Slave	$t_{lag}$	1/2 1	— —	$t_{sck}$ $t_{cyc}$
4	Clock (SCK) High or Low Time Master Slave	$t_{wsck}$	$t_{cyc} - 60$ $t_{cyc} - 30$	$128 t_{cyc}$ —	ns ns
5	Sequential Transfer Delay Master Slave	$t_{td}$	1/2 1	— —	$t_{sck}$ $t_{cyc}$
6	Data Setup Time (Inputs) Master Slave	$t_{su}$	30 30	— —	ns ns
7	Data Hold Time (Inputs) Master Slave	$t_{hi}$	0 30	— —	ns ns
8	Slave Access Time	$t_a$	—	1	$t_{cyc}$
9	Slave MISO Disable Time	$t_{dis}$	—	1	$t_{cyc}$
10	Data Valid (after SCK Edge) Master Slave	$t_v$	— —	50 50	ns ns
11	Data Hold Time (Outputs) Master Slave	$t_{ho}$	0 0	— —	ns ns
12	Rise Time Input Output	$t_{ri}$ $t_{ro}$	— —	$t_{cyc} - 30$ 30	ns ns
13	Fall Time Input Output	$t_{fi}$ $t_{fo}$	— —	$t_{cyc} - 30$ 30	ns ns

## NOTES:

1. All AC timing is shown with respect to 20%  $V_{DD}$  and 70%  $V_{DD}$  levels unless otherwise noted.

PRELIMINARY

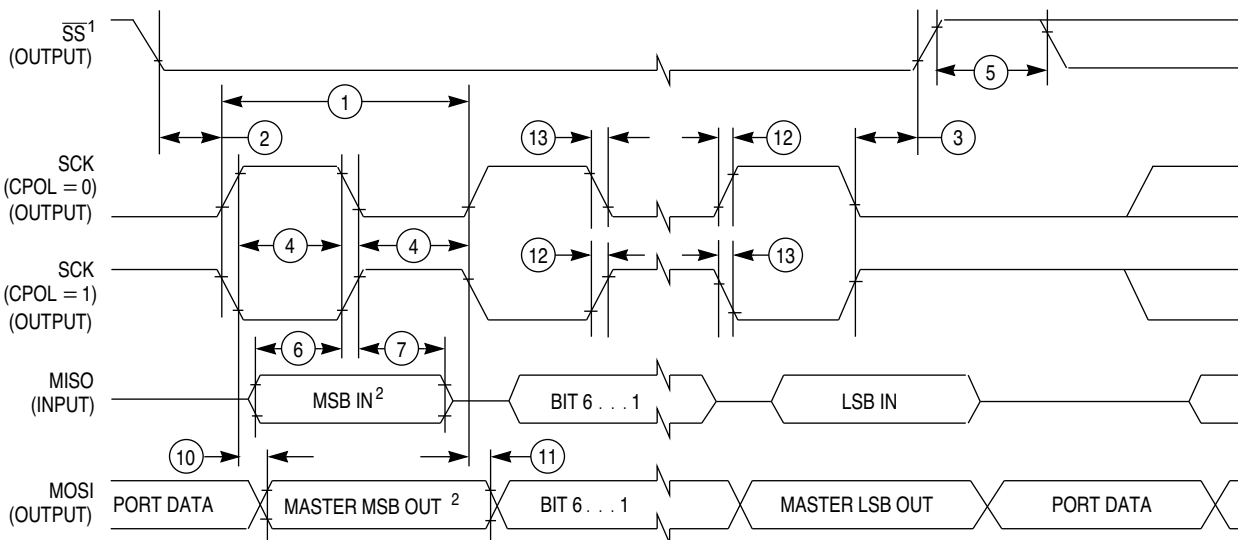




1.  $\overline{SS}$  output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

SPI MASTER CPHA0

**A) SPI Master Timing (CPHA = 0)**

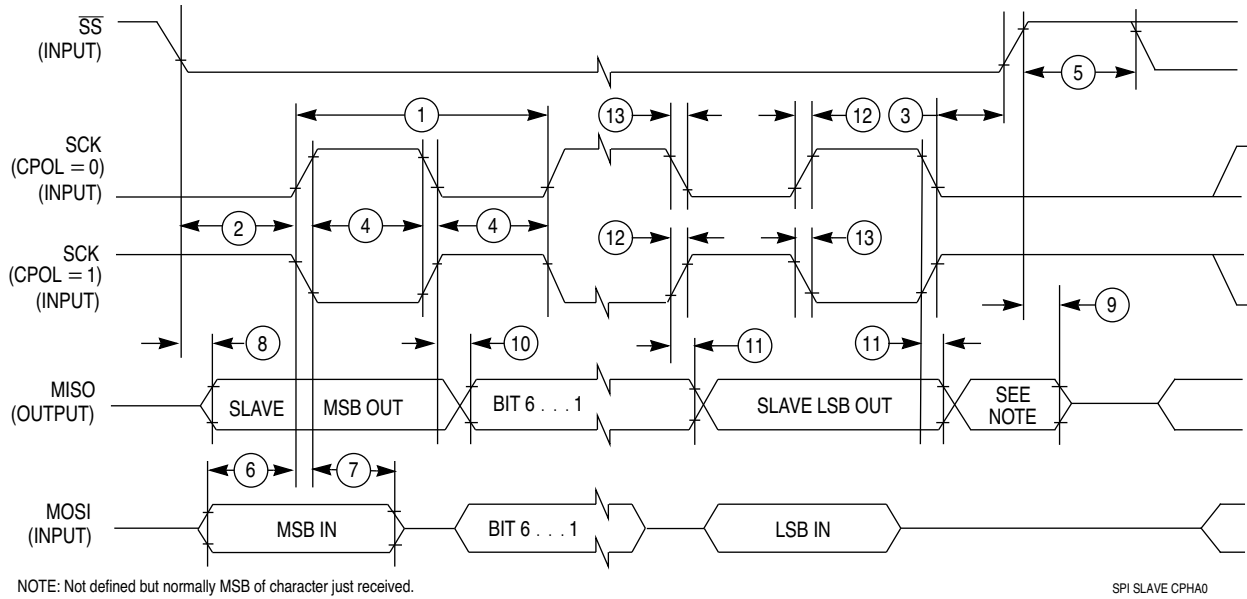


1.  $\overline{SS}$  output mode (DDS7 = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

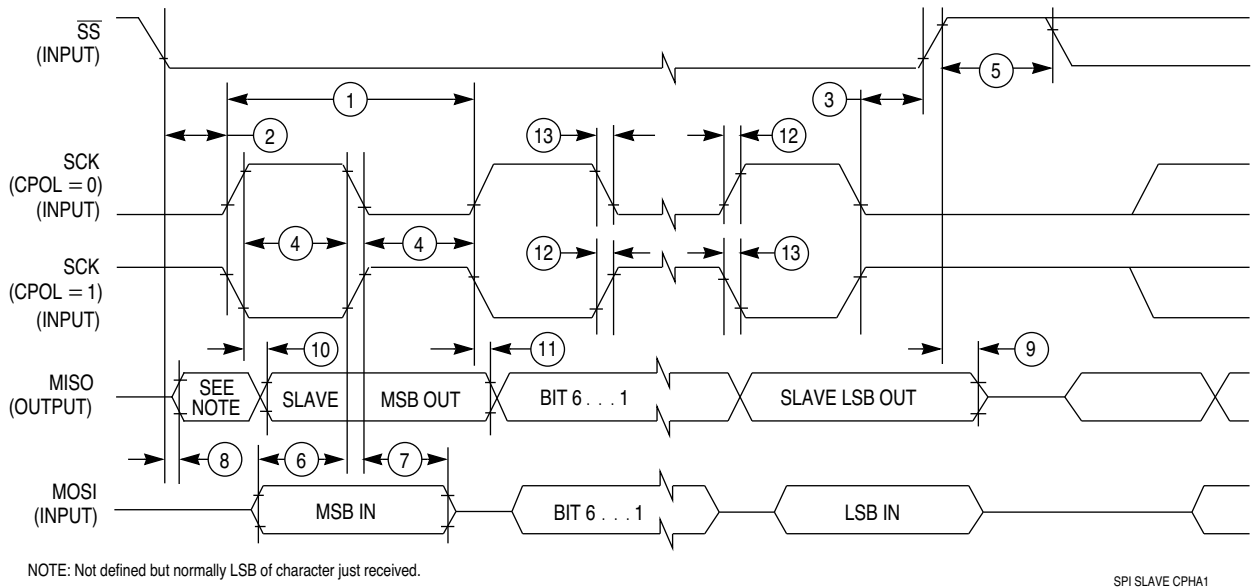
SPI MASTER CPHA1

**B) SPI Master Timing (CPHA = 1)**

**Figure 9 SPI Timing Diagram (1 of 2)**



**A) SPI Slave Timing (CPHA = 0)**



**B) SPI Slave Timing (CPHA = 1)**

**Figure 10 SPI Timing Diagram (2 of 2)**